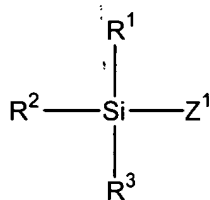
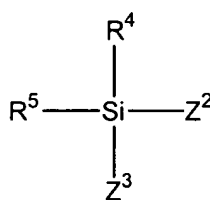


Amendments to the Claims:

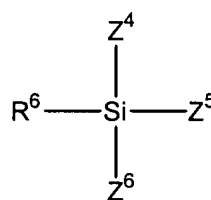
1. (Currently amended) A composition for forming a porous film comprising 10ppm or less halogen impurity and 10ppb or less metallic impurity where boron is counted in the metallic impurity, the composition comprising a ~~being prepared by~~ hydrolysis and condensation product of an alkoxy silane or a partial hydrolysis product of the alkoxy silane in an organic solvent in the presence of trialkylmethylammonium hydroxide as a catalyst, wherein the alkoxy silane comprises ~~is~~ one or more alkoxysilanes selected from the groups consisting of compounds represented by formulae (1) to (4) below, and the trialkylmethylammonium hydroxide is represented by formula (5) below,



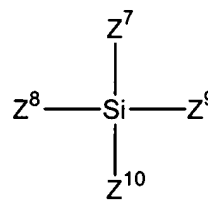
(1)



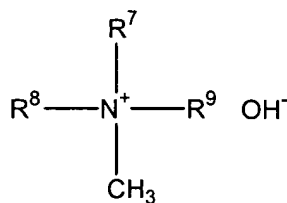
(2)



(3)



(4)



(5)

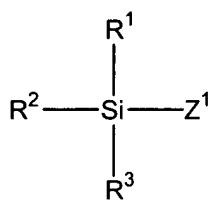
wherein  $\text{Z}^1, \text{Z}^2, \text{Z}^3, \text{Z}^4, \text{Z}^5, \text{Z}^6, \text{Z}^7, \text{Z}^8, \text{Z}^9$  and  $\text{Z}^{10}$  each independently represents an alkoxy group having 1 to 6 carbons;  $\text{R}^1, \text{R}^2, \text{R}^3, \text{R}^4, \text{R}^5$  and  $\text{R}^6$  each independently represents a monovalent hydrocarbon group which ~~may or may not be~~ is optionally substituted; and  $\text{R}^7, \text{R}^8$  and  $\text{R}^9$  each independently represents an alkyl group having 1 to 6 carbons.

2. (Currently amended) The composition for forming a porous film according to Claim 1 wherein the total carbon number of  $R^7$ ,  $R^8$  and  $R^9$  in said trialkylmethylammonium hydroxide is 4 to 15.

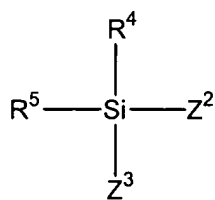
3. (Currently amended) The composition for forming a porous film according to Claim 1 ~~or 2~~ wherein said trialkylmethylammonium comprises ~~has been formed with a reaction product of between~~ trialkylamine and dimethyl carbonate.

4. (Currently amended) The composition for forming a porous film according to ~~any one of Claims 1 to 2~~, wherein said hydrolysis and condensation product of an alkoxysilane or the partial hydrolysis product of the alkoxysilane comprises ~~yields~~ a product having a weight-average molecular weight of 10,000 to 1,000,000.

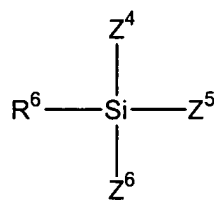
5. (Currently amended) A method for manufacturing a composition for forming a porous film, comprising ~~a step of hydrolysis and condensation of~~ hydrolysing and condensing an alkoxysilane or a partial hydrolysis product of the alkoxysilane in an organic solvent in the presence of trialkylmethylammonium hydroxide as a catalyst, wherein the alkoxysilane comprises is one or more alkoxysilanes selected from the group consisting of compounds represented by formulae (1) to (4) below, and the trialkylmethylammonium hydroxide is represented by formula (5) below which is a reaction product of ~~between~~ trialkylamine and dimethyl carbonate,



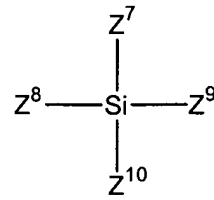
(1)



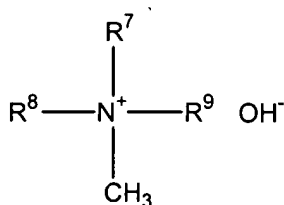
(2)



(3)



(4)



(5)

wherein  $\text{Z}^1, \text{Z}^2, \text{Z}^3, \text{Z}^4, \text{Z}^5, \text{Z}^6, \text{Z}^7, \text{Z}^8, \text{Z}^9$  and  $\text{Z}^{10}$  each independently represents an alkoxy group having 1 to 6 carbons;  $\text{R}^1, \text{R}^2, \text{R}^3, \text{R}^4, \text{R}^5$  and  $\text{R}^6$  each independently represents a monovalent hydrocarbon group which ~~may or may not be~~ is optionally substituted; and  $\text{R}^7, \text{R}^8$  and  $\text{R}^9$  each independently represents an alkyl group having 1 to 6 carbons.

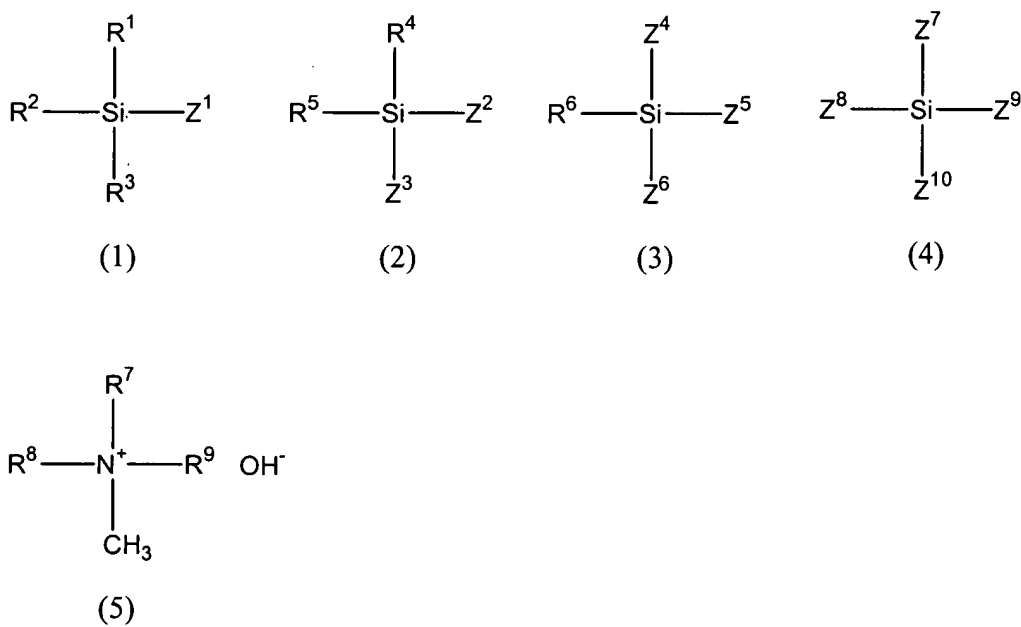
6. (Currently amended) A method for manufacturing a porous film comprising ~~steps of applying said a composition according to any one of Claims 1 to 2 to a substrate so as to form a film thereon, drying the film and heating the dried film so as to produce a porous film.~~

7. (Currently amended) A porous film comprising a formable by said composition according to ~~any one of Claims 1 to 2.~~

8. (Currently amended) An interlevel insulating film comprising a formed by said composition according to ~~any one of Claims 1 to 2.~~

9. (Currently amended) A semiconductor device comprising a porous film therein, the porous film formed of ~~being formable by~~ a composition comprising 10ppm or less halogen

impurity and 10ppb or less metallic impurity where boron is counted in the metallic impurity, the composition comprising the ~~being prepared by~~ hydrolysis and condensation product of an alkoxysilane or a partial hydrolysis product of the alkoxysilane in an organic solvent in the presence of trialkylmethyammonium hydroxide as a catalyst, wherein the alkoxysilane comprises is one or more alkoxysilanes selected from the group consisting of compounds represented by formulae (1) to (4) below, and the trialkylmethyammonium hydroxide is represented by formula (5) below,



wherein  $\text{Z}^1, \text{Z}^2, \text{Z}^3, \text{Z}^4, \text{Z}^5, \text{Z}^6, \text{Z}^7, \text{Z}^8, \text{Z}^9$  and  $\text{Z}^{10}$  each independently represents an alkoxy group having 1 to 6 carbons;  $\text{R}^1, \text{R}^2, \text{R}^3, \text{R}^4, \text{R}^5$  and  $\text{R}^6$  each independently represents a monovalent hydrocarbon group which ~~may or may not be~~ is optionally substituted; and  $\text{R}^7, \text{R}^8$  and  $\text{R}^9$  each independently represents an alkyl group having 1 to 6 carbons.

10. (Currently amended) The semiconductor device according to Claim 9 wherein the total carbon number of  $\text{R}^7, \text{R}^8$  and  $\text{R}^9$  in said trialkylmethyammonium hydroxide is 4 to 15.

11. (Currently amended) The semiconductor device according to Claim 9 ~~or 10~~ wherein said trialkylmethylammonium hydroxide comprises ~~has been formed with a reaction product of between~~ trialkylamine and dimethyl carbonate.

12. (Currently amended) The semiconductor device according to ~~any one of~~ Claims 9 ~~to 10~~ wherein said hydrolysis and condensation product of an alkoxysilane or the partial hydrolysis product of the alkoxysilane comprises ~~yields~~ a product having a weight-average molecular weight of 10,000 to 1,000,000.

13. (Currently amended) The semiconductor device according to ~~any one of~~ Claims 9 ~~to 10~~ wherein said porous film is between metal interconnections in a same layer or multi-level interconnects, or is between upper and lower metal interconnection layers.